

AMENDMENTS TO THE SPECIFICATION

Please replace Paragraph [0051] with the following paragraph rewritten in amendment format:

The leak current of the nMOSFET with the structure of $X_j = 10$ nm is reduced, in effect, by about four digits compared to the leak current of the nMOSFET with the structure of $X_j = 25$ nm, and by about two digits compared to the leak current of the nMOSFET with the structure of $X_j = 20$ nm, ~~which are nMOSFETS with the conventional single-drain structure.~~